# Sprawozdanie 3

#### Jan Bronicki

#### 1 Cel ćwiczenia

Cel ćwiczenia to obliczenie parametrów, przeprowadzenie symulacji oraz wyznaczenie wykresów charakteryzujączych układy sterowania NPN i PNP (4-20 mA).

Dobrane 3 różne wartości  $R_{pom}$  to  $10\Omega,50\Omega,250\Omega.$  Rezystancja obiciążenie  $R_{obc}=1k\Omega.$ 

## 2 Moduł 4-20mA, Tranzystor NPN

#### 2.1 $R_{pom}$

Napięcia do sterowania:

 $U_{pom,4mA} = 4mA \cdot 10\Omega = 0.04V$ 

 $U_{pom,20mA} = 20mA \cdot 10\Omega = 0.2V$ 

Dobranie rezystorów (prad  $I_1 = 4mA$ ):

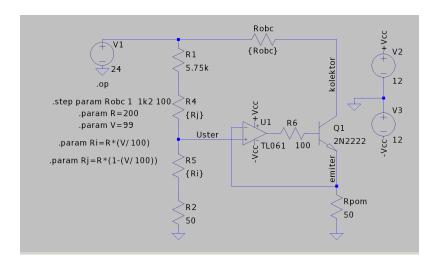
$$R_1 = \frac{23.8V}{4mA} = 5.95k\Omega$$

$$R_2 = \frac{0.04V}{4mA} = 10\Omega$$

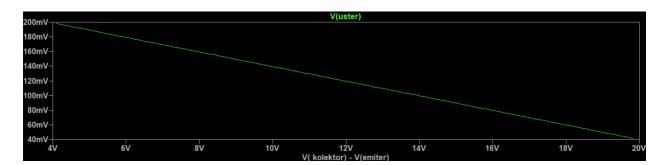
$$R_{ptm} = \frac{0.16V}{4mA} = 40\Omega$$

$$R_{MAX,4mA} = \frac{24V - 0.1V - 0.04V}{4mA} = 5965\Omega$$

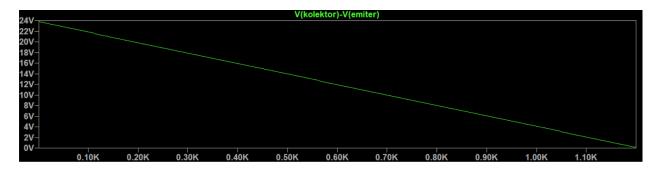
$$R_{MAX,20mA} = \frac{24V - 0.1V - 0.2V}{20mA} = 1193\Omega$$



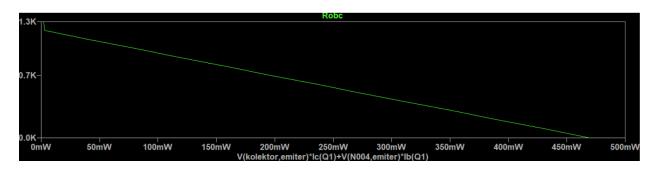
Rysunek 1: Schemat NPN



Rysunek 2:  $U_{ster}(U_{ce})$ 



Rysunek 3:  $U_{ce}(R_{obc})$ 



Rysunek 4:  $R_{obc}(P_{diss})$ 

#### **2.2** $R_{pom} = 50\Omega$

Napięcia sterujące układem:

$$U_{pom,4mA}=4mA\cdot 50\Omega=0.2V$$

$$U_{pom,20mA} = 20mA \cdot 50\Omega = 1V$$

Dobranie rezystorów (przyjmuję prąd  $I_1 = 4mA$ ):

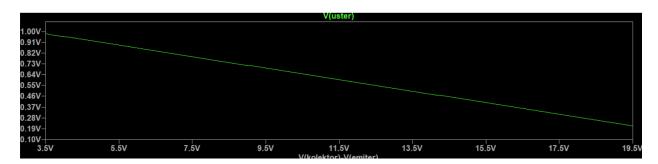
$$R_1 = \frac{23V}{4mA} = 5.75k\Omega$$

$$R_2 = \frac{0.2V}{4mA} = 50\Omega$$

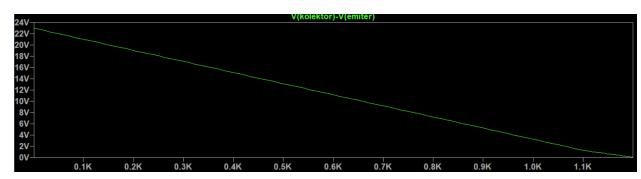
$$R_{ptn} = \frac{0.8V}{4mA} = 200\Omega$$

$$R_{MAX,4mA} = \frac{24V - 0.1V - 0.2V}{4mA} 5925\Omega$$

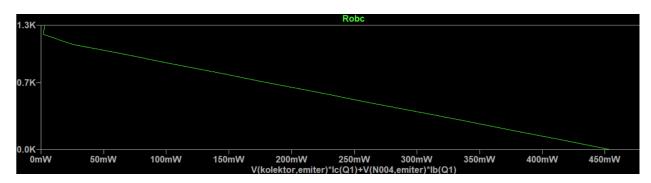
$$R_{MAX,20mA} = \frac{24V - 0.1V - 1V}{20mA} 1145\Omega$$



Rysunek 5:  $U_{strer}(U_{ce})$ 



Rysunek 6:  $U_{ce}(R_{obc})$ 



Rysunek 7:  $R_{obc}(P_{diss})$ 

## $R_{pom} = 250\Omega$

Napięcia sterujące:

 $U_{pom,4mA} = 4mA \cdot 250\Omega = 1V$   $U_{pom,20mA} = 20mA \cdot 250\Omega = 5V$ Dobranie rezystorów  $(I_1 = 4mA)$ :

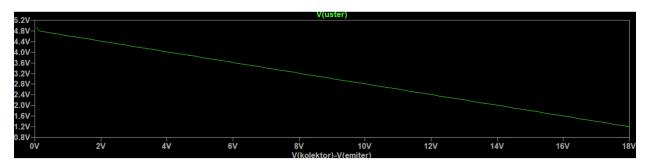
$$R_1 = \frac{19V}{4mA} = 4.75k\Omega$$

$$R_2 = \frac{1V}{4mA} 250\Omega$$

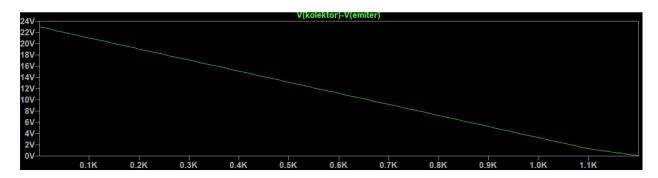
$$R_{ptn} = \frac{4V}{4mA} = 1k\Omega$$

$$R_{MAX,4ma} = \frac{24V - 0.1V - 1V}{4mA} = 5725\Omega$$

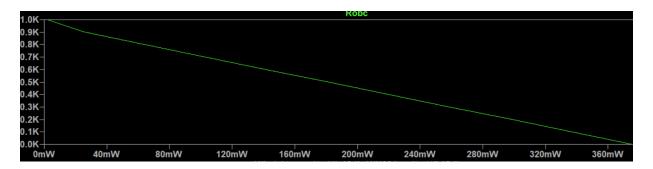
$$R_{MAX,20mA} = \frac{24V - 0.1V - 5V}{20mA} = 945\Omega$$



Rysunek 8:  $U_{strer}(U_{ce})$ 

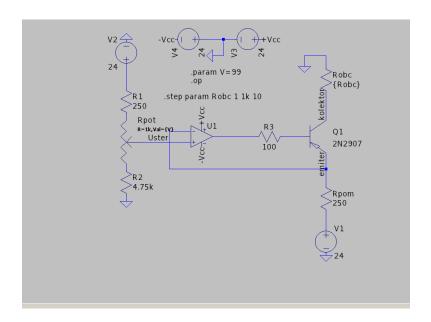


Rysunek 9:  $U_{ce}(R_{obc})$ 



Rysunek 10:  $R_{obc}(P_{diss})$ 

# 3 Moduł 4-20mA, Tranzystor PNP



Rysunek 11: Układ z tranzystorem PNP

## **3.1** $R_{pom} = 10\Omega$

Napięcia sterujące:

 $U_{pom,4mA} = 24V - 4mA \cdot 10\Omega = 23.96V$ 

 $U_{pom,20mA} = 24V - 20mA \cdot 10\Omega = 23.98V$ 

Dobranie rezystorów ( $I_1 = 4mA$ ):

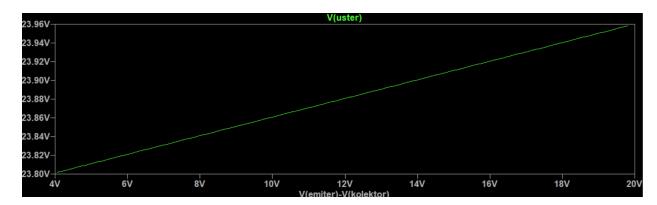
$$R_1 = \frac{0.04V}{4mA} = 10\Omega$$

$$R_2 = \frac{23.8V}{4mA} = 5.95k\Omega$$

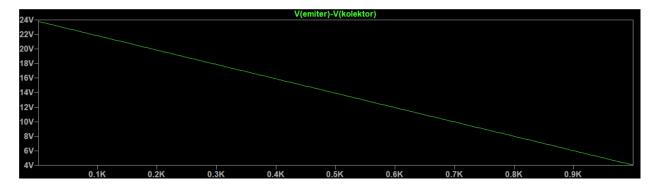
$$R_{ptn} = \frac{0.16}{4mA} = 40\Omega$$

$$R_{MAX,4mA} = \frac{24V - 0.1V - 0.04V}{4mA} = 5965\Omega$$

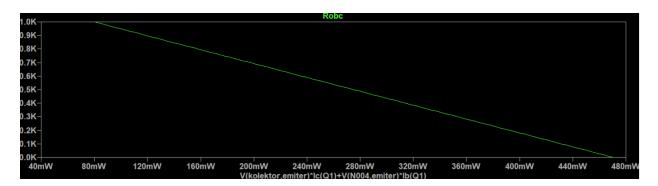
$$R_{MAX,20mA} = \frac{24V - 0.1V - 0.2V}{20mA} = 1193\Omega$$



Rysunek 12:  $U_{strer}(U_{ce})$ 



Rysunek 13:  $U_{ce}(R_{obc})$ 



Rysunek 14:  $R_{obc}(P_{diss})$ 

#### $R_{pom} = 50\Omega$ 3.2

Napięcia sterowania:

$$U_{\text{norm 4m A}} = 24V - 4mA \cdot 50\Omega = 23.80V$$

$$\begin{split} U_{pom,4mA} &= 24V - 4mA \cdot 50\Omega = 23.80V \\ U_{pom,20mA} &= 24V - 20mA \cdot 50\Omega = 23V \end{split}$$

Dobranie rezystorów  $(I_1 = 4mA)$ :

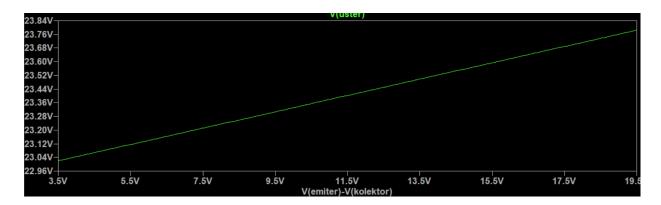
$$R_1 = \frac{0.02V}{4mA} = 50\Omega$$

$$R_2 = \frac{23V}{4mA} = 5.75k\Omega$$

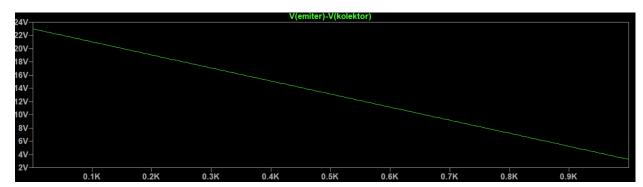
$$R_{ptn} = \frac{0.8V}{4mA} = 200\Omega$$

$$R_{MAX,4mA} = \frac{24V - 0.1V - 0.2V}{4mA} = 5925\Omega$$

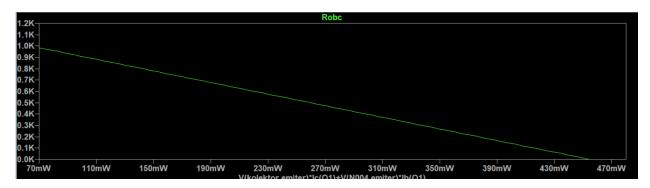
$$R_{MAX,20mA} = \frac{24V - 0.1V - 1V}{20mA} = 1145\Omega$$



Rysunek 15:  $U_{strer}(U_{ce})$ 



Rysunek 16:  $U_{ce}(R_{obc})$ 



Rysunek 17:  $R_{obc}(P_{diss})$ 

## **3.3** $R_{pom} = 250\Omega$

Napięcia sterowania:

 $U_{pom,4mA} = 24V - 4mA \cdot 250\Omega = 23V$ 

$$U_{pom,20mA} = 24V - 20mA \cdot 250\Omega = 19V$$

Dobranie rezystorów  $(I_1 = 4mA)$ :

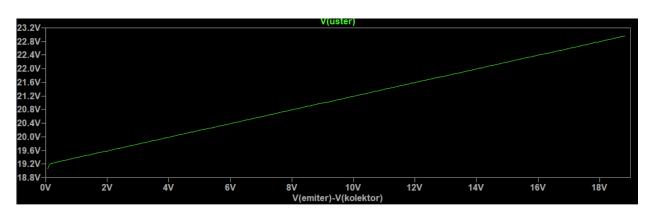
$$R_1 = \frac{1V}{4mA} = 250\Omega$$

$$R_2 = \frac{19V}{4mA} = 4.75k\Omega$$

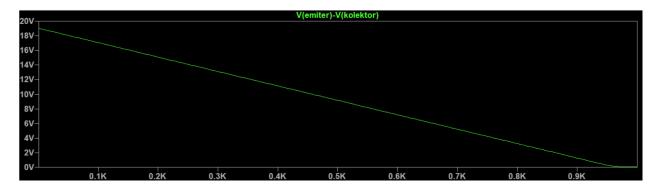
$$R_{ptn} = \frac{4V}{4mA} = 1k\Omega$$

$$R_{MAX,4mA} = \frac{24V - 0.1V - 1V}{4mA} = 5725\Omega$$

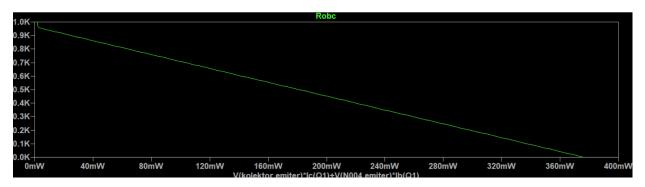
$$R_{MAX,20mA} = \frac{24V - 0.1V - 5V}{20mA} = 945\Omega$$



Rysunek 18:  $U_{strer}(U_{ce})$ 



Rysunek 19:  $U_{ce}(R_{obc})$ 



Rysunek 20:  $R_{obc}(P_{diss})$ 

## 4 Wnioski

Układami z tranzystorami NPN można dobrze sterować na niższych napięciach niż układami z tranzystorami PNP. Maxymalne wartości rezystancji obciążenia dla  $R_{pom}$  są identyczne dla układów z tranzystorem NPN i PNP, dlatego układy są symetryczne. Sterowanie potencjometrem jest odwrotne w zależności od użytego tranzystora.